

Ian T Ferguson

List of Publications by Year in descending order

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67
papers

709
citations

567281

15
h-index

580821

25
g-index

68
all docs

68
docs citations

68
times ranked

870
citing authors

#	ARTICLE	IF	CITATIONS
1	A comparative investigation of the optical properties of polar and semipolar GaN epi-films grown by metalorganic chemical vapor deposition. <i>Semiconductor Science and Technology</i> , 2022, 37, 065021.	2.0	1
2	Comparative spectroscopic studies of MOCVD grown AlN films on Al ₂ O ₃ and 6H-SiC. <i>Journal of Alloys and Compounds</i> , 2021, 857, 157487.	5.5	28
3	Effects of thickness and interlayer on optical properties of AlN films at room and high temperature. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021, 39, .	2.1	9
4	Enhancement in electrical and optical properties of field-effect passivated GaN blue light emitting diodes. <i>Semiconductor Science and Technology</i> , 2021, 36, 115018.	2.0	4
5	Field-effect passivation of metal/ <i>n</i> -GaAs Schottky junction solar cells using atomic layer deposited Al ₂ O ₃ /ZnO ultrathin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020, 38, .	2.1	16
6	XPS characterization of Al ₂ O ₃ /ZnO ultrathin films grown by atomic layer deposition. <i>Surface Science Spectra</i> , 2020, 27, 024012.	1.3	2
7	Effects of annealing temperature, thickness and substrates on optical properties of m-plane ZnO films studied by photoluminescence and temperature dependent ellipsometry. <i>Journal of Alloys and Compounds</i> , 2020, 848, 156631.	5.5	11
8	Structural and optical properties of (Zn,Mn)O thin films prepared by atomic layer deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020, 38, 042408.	2.1	11
9	Strain-stress study of Al _x Ga _{1-x} N/AlN heterostructures on c-plane sapphire and related optical properties. <i>Scientific Reports</i> , 2019, 9, 10172.	3.3	24
10	Investigation of the Optical Properties of InSb Thin Films Grown on GaAs by Temperature-Dependent Spectroscopic Ellipsometry. <i>Journal of Applied Spectroscopy</i> , 2019, 86, 276-282.	0.7	2
11	Neutron detection performance of gallium nitride based semiconductors. <i>Scientific Reports</i> , 2019, 9, 17551.	3.3	10
12	Surface and optical properties of indium-rich InGaN layers grown on sapphire by migration-enhanced plasma assisted metal organic chemical vapor deposition. <i>Materials Research Express</i> , 2019, 6, 016407.	1.6	4
13	Room Temperature Ferromagnetism in Gadolinium-doped Gallium Nitride. <i>MRS Advances</i> , 2018, 3, 159-164.	0.9	4
14	Influence of high-temperature AlN intermediate layer on the optical properties of MOCVD grown AlGa _N films. <i>Materials Research Express</i> , 2017, 4, 025903.	1.6	1
15	Composition and temperature dependent optical properties of Al _x Ga _{1-x} N alloy by spectroscopic ellipsometry. <i>Applied Surface Science</i> , 2017, 421, 389-396.	6.1	36
16	Review—The Current and Emerging Applications of the III-Nitrides. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, Q149-Q156.	1.8	72
17	The structural properties of InGa _N alloys and the interdependence on the thermoelectric behavior. <i>AIP Advances</i> , 2016, 6, .	1.3	32
18	X-ray absorption fine structure of ZnO thin film on Si and sapphire grown by MOCVD. , 2016, , .		1

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19	Investigation of Thermoelectric Properties of P-Type GaN Thin Films. Materials Research Society Symposia Proceedings, 2015, 1774, 13-18.	0.1	0
20	Thermoelectric Properties of ZnO Thin Films Grown by Metal-Organic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 2015, 1805, 1.	0.1	3
21	Structural and optical analyses of Al _x Ga _{1-x} N thin films grown by metal organic chemical vapor deposition. Japanese Journal of Applied Physics, 2015, 54, 02BA05.	1.5	6
22	Room-temperature thermoelectric properties of GaN thin films grown by metal organic chemical vapor deposition. Wuli Xuebao/Acta Physica Sinica, 2015, 64, 047202.	0.5	0
23	Spatial analysis of ZnO thin films prepared by vertically aligned MOCVD. , 2014, , .		7
24	Characterization of undoped and Si-doped bulk GaN fabricated by hydride vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 573-576.	0.8	6
25	Thermoelectric Properties of Undoped and Si-doped Bulk GaN. Materials Research Society Symposia Proceedings, 2013, 1558, 1.	0.1	3
26	GaN-Based Neutron Scintillators with a ⁶ LiF Conversion Layer. Materials Research Society Symposia Proceedings, 2012, 1396, .	0.1	2
27	Optical absorption dependence on composition and thickness of In _x Ga _{1-x} N (0.05$\leq x \leq 0.22$) grown on GaN/sapphire. Thin Solid Films, 2012, 520, 6807-6812.	1.8	4
28	Comparison of neutron conversion layers for GaN-based scintillators. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 957-959.	0.8	15
29	Mechanism for THz generation from InN micropylamid emitters. Journal of Applied Physics, 2011, 109, 093111.	2.5	10
30	Thermopower Study of GaN-Based Materials for Next-Generation Thermoelectric Devices and Applications. Journal of Electronic Materials, 2011, 40, 513-517.	2.2	44
31	Electrical and magnetic properties of Ga _{1-x} GdxN grown by metal organic chemical vapor deposition. Journal of Applied Physics, 2011, 110, .	2.5	20
32	Ga _{1-x} GdxN-Based Spin Polarized Light Emitting Diode. Materials Research Society Symposia Proceedings, 2011, 1290, 1.	0.1	2
33	Seebeck and Spin Seebeck effect in Gd-doped GaN thin films for Thermoelectric Devices and Applications. Materials Research Society Symposia Proceedings, 2011, 1329, 1.	0.1	1
34	Compositional instability in strained InGaN epitaxial layers induced by kinetic effects. Journal of Applied Physics, 2011, 110, .	2.5	32
35	Growth of pattern-free InN micropylamids by metalorganic chemical vapor deposition. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1895-1899.	1.8	4
36	Design and Realization of Wide-Band-Gap (~ 2.67 eV) InGaN p-n Junction Solar Cell. IEEE Electron Device Letters, 2010, 31, 32-34.	3.9	65

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37	Metal organic chemical vapor deposition of crack-free GaN-based light emitting diodes on Si (111) using a thin Al ₂ O ₃ interlayer. Applied Physics Letters, 2009, 94, 222105.	3.3	15
38	Crystalline Perfection of Epitaxial Structure: Correlations with Composition, Thickness, and Elastic Strain of Epitaxial Layers. Materials Research Society Symposia Proceedings, 2009, 1167, 4.	0.1	0
39	Utilizing Polarization Induced Band Bending for InGa _N Solar Cell Design. Materials Research Society Symposia Proceedings, 2009, 1167, 4.	0.1	3
40	Raman scattering study on anisotropic property of wurtzite GaN. Journal of Applied Physics, 2009, 105, 036102.	2.5	28
41	GaN-Based heterojunction structures for ultraviolet/infrared dual-band detection. , 2009, , .		2
42	Growth and magnetization study of transition metal doped GaN nanostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1740-1742.	0.8	3
43	The effect of silicon doping in the selected barrier on the electroluminescence of InGa _N •GaN multiquantum well light emitting diode. Applied Physics Letters, 2007, 90, 031102.	3.3	33
44	Photoluminescence characteristics of InAs self-assembled quantum dots in InGaAs•GaAs quantum well. Journal of Applied Physics, 2007, 101, 126101.	2.5	14
45	Reflective second harmonic generation from ZnO thin films: A study on the Zn•O bonding. Applied Physics Letters, 2007, 90, 161904.	3.3	23
46	NITRIDE BASED SCHOTTKY-BARRIER PHOTOVOLTAIC DEVICES. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	1
47	InGa _N Light-Emitting Diode With Quasi-Quantum-Dot-Shaped Active Layer Using SiCN Interfacial Layer. IEEE Photonics Technology Letters, 2007, 19, 24-26.	2.5	3
48	Correlation of the structural and ferromagnetic properties of Ga _{1-x} Mn _x N grown by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2006, 287, 591-595.	1.5	28
49	High quality tin zinc oxide/Ag ohmic contacts for UV flip-chip light-emitting diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2133-2136.	0.8	1
50	Low resistance and highly reflective ohmic contacts top -type GaN using transparent interlayers for flip-chip light emitting diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2207-2210.	0.8	0
51	Alloying, co-doping, and annealing effects on the magnetic and optical properties of MOCVD-grown Ga _{1-x} Mn _x N. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 126, 230-235.	3.5	16
52	A nucleation study of group III-nitride multifunctional nanostructures. Journal of Crystal Growth, 2006, 287, 596-600.	1.5	11
53	THE GROWTH AND CHARACTERIZATION OF ROOM TEMPERATURE FERROMAGNETIC WIDEBAND-GAP MATERIALS FOR SPINTRONIC APPLICATIONS. International Journal of High Speed Electronics and Systems, 2006, 16, 515-543.	0.7	1
54	Transition Metal-Doped ZnO: A Comparison of Optical, Magnetic, and Structural Behavior of Bulk and Thin Films. Materials Research Society Symposia Proceedings, 2006, 957, 1.	0.1	2

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55	Comparison of the Incorporation of Various Transition Metals into GaN by MOCVD. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
56	Structural and Magnetic Characterization of MOCVD Grown GaMnN and GaFeN Nanostructures. Materials Research Society Symposia Proceedings, 2006, 959, 1.	0.1	0
57	InGaN-light emitting diode with high density truncated hexagonal pyramid shaped p-GaN hillocks on the emission surface. Applied Physics Letters, 2006, 89, 251106.	3.3	23
58	THE GROWTH AND CHARACTERIZATION OF ROOM TEMPERATURE FERROMAGNETIC WIDEBAND-GAP MATERIALS FOR SPINTRONIC APPLICATIONS. , 2006, , .		1
59	Metal Organic Chemical Vapor Deposition Growth of GaN and GaMnN Multifunctional Nanostructures. Materials Research Society Symposia Proceedings, 2005, 901, 1.	0.1	2
60	Towards a Novel Broadband Spectrally Dynamic Solid State Light Source. Materials Research Society Symposia Proceedings, 2005, 892, 17.	0.1	0
61	Optimization of Growth and Activation of Highly Doped p-type GaN for Tunnel Junctions. Materials Research Society Symposia Proceedings, 2004, 831, 132.	0.1	0
62	Optical and Structural Investigations on Mn-Ion States in MOCVD-grown Ga _{1-x} Mn _x N. Materials Research Society Symposia Proceedings, 2004, 831, 61.	0.1	1
63	A Nucleation Study of GaN Multifunctional Nanostructures. Materials Research Society Symposia Proceedings, 2004, 831, 254.	0.1	1
64	Impact of Manganese incorporation on the structural and magnetic properties of MOCVD-grown Ga _{1-x} Mn _x N. Materials Research Society Symposia Proceedings, 2004, 831, 708.	0.1	1
65	Development of Dual MQW Region LEDs for General Illumination. Materials Research Society Symposia Proceedings, 2004, 831, 79.	0.1	0
66	Epitaxial film growth and characterization. Thin Films, 2001, 28, 1-69.	0.1	1
67	MOCVD growth and characterization of 100-mm diameter (Ga _{1-x} Al _x) _{0.5} In _{0.5} P/GaAs epitaxial materials for LED applications. , 1998, 3279, 161.		2